

# MMBD7000L, SMMBD7000L

## Dual Switching Diode

### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS (EACH DIODE)

| Rating  | Symbol    | Value | Unit |
|---|-----------|-------|------|
| Reverse Voltage   | $V_R$     | 100   | V    |
| Forward Current   | $I_F$     | 200   | mA   |
| Forward Surge Current<br>(60 Hz @ 1 cycle)                                | $I_{FSM}$ | 1.6   | A    |
| Repetitive Peak Forward Current<br>(Pulse Wave = 1 sec, Duty Cycle = 66%) | $I_{FRM}$ | 0.5   | A    |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

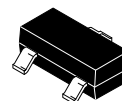
| Characteristic   | Symbol          | Max         | Unit                      |
|--|-----------------|-------------|---------------------------|
| Total Device Dissipation FR-5 Board<br>(Note 1) $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$            | $P_D$           | 225         | mW                        |
|  |                 | 1.8         | mW/ $^\circ\text{C}$      |
| Thermal Resistance, Junction to Ambient  | $R_{\theta JA}$ | 556         | $^\circ\text{C}/\text{W}$ |
| Total Device Dissipation<br>Alumina Substrate, (Note 2)<br>$T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$           | 300         | mW                        |
|  |                 | 2.4         | mW/ $^\circ\text{C}$      |
| Thermal Resistance,<br>Junction-to-Ambient   | $R_{\theta JA}$ | 417         | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature   | $T_J, T_{stg}$  | -55 to +150 | $^\circ\text{C}$          |

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

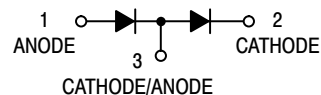


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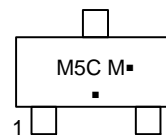
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SOT-23 (TO-236)  
CASE 318  
STYLE 11



### MARKING DIAGRAM



M5C = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

| Device        | Package             | Shipping†               |
|---------------|---------------------|-------------------------|
| MMBD7000LT1G  | SOT-23<br>(Pb-Free) | 3,000 /<br>Tape & Reel  |
| SMMBD7000LT1G | SOT-23<br>(Pb-Free) | 3,000 /<br>Tape & Reel  |
| MMBD7000LT3G  | SOT-23<br>(Pb-Free) | 10,000 /<br>Tape & Reel |
| SMMBD7000LT3G | SOT-23<br>(Pb-Free) | 10,000 /<br>Tape & Reel |

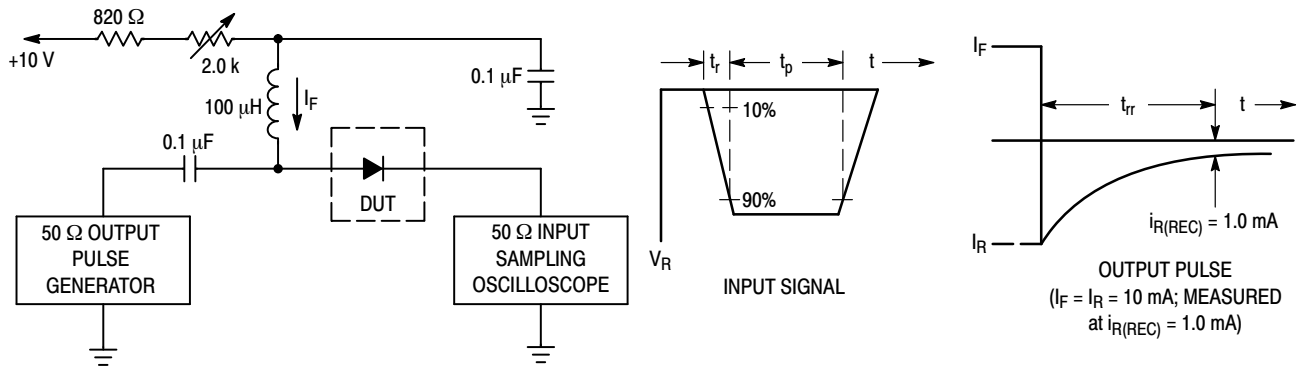
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBD7000L, SMMBD7000L

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

| Characteristic  | Symbol                        | Min                  | Max                | Unit          |
|---|-------------------------------|----------------------|--------------------|---------------|
| <b>OFF CHARACTERISTICS</b>  |                               |                      |                    |               |
| Reverse Breakdown Voltage<br>( $I_{BR} = 100 \mu\text{A}$ )   | $V_{(BR)}$                    | 100                  | -                  | Vdc           |
| Reverse Voltage Leakage Current<br>( $V_R = 50 \text{ Vdc}$ )<br>( $V_R = 100 \text{ Vdc}$ )<br>( $V_R = 50 \text{ Vdc}, 125^\circ\text{C}$ ) | $I_R$<br>$I_{R2}$<br>$I_{R3}$ | -<br>-<br>-          | 1.0<br>3.0<br>100  | $\mu\text{A}$ |
| Forward Voltage<br>( $I_F = 1.0 \text{ mA}$ )<br>( $I_F = 10 \text{ mA}$ )<br>( $I_F = 100 \text{ mA}$ )                                      | $V_F$                         | 0.55<br>0.67<br>0.75 | 0.7<br>0.82<br>1.1 | Vdc           |
| Reverse Recovery Time<br>( $I_F = I_R = 10 \text{ mA}$ ) (Figure 1)   | $t_{rr}$                      | -                    | 4.0                | ns            |
| Capacitance ( $V_R = 0 \text{ V}$ )   | C                             | -                    | 1.5                | pF            |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

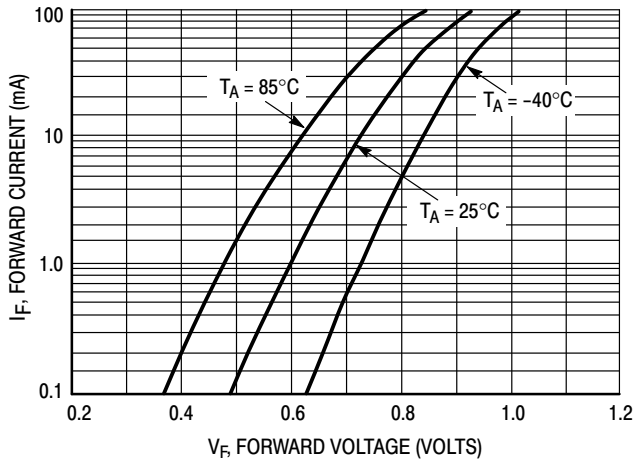


- Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current ( $I_F$ ) of 10 mA.  
 2. Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 10 mA.  
 3.  $t_p \gg t_{rr}$

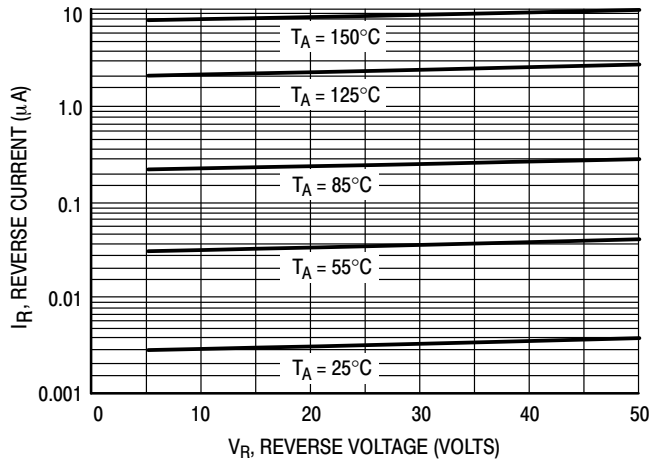
**Figure 1. Recovery Time Equivalent Test Circuit**

# MMBD7000L, SMMBD7000L

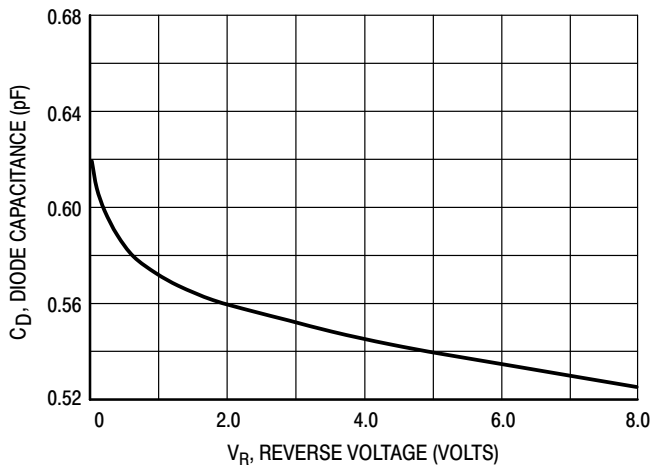
## CURVES APPLICABLE TO EACH DIODE



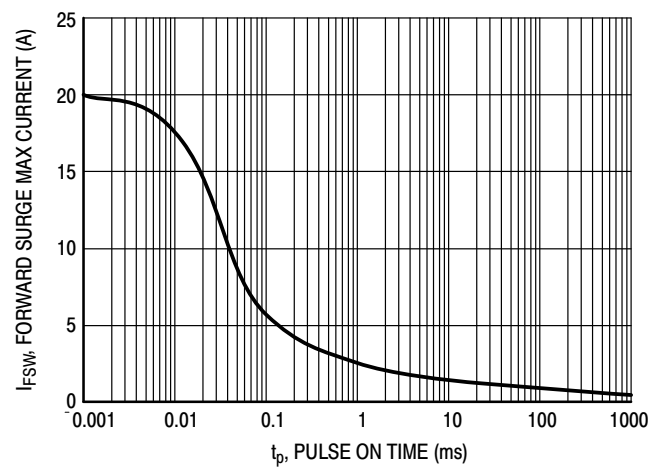
**Figure 2. Forward Voltage**



**Figure 3. Leakage Current**



**Figure 4. Capacitance**

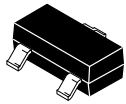


**Figure 5. Forward Surge Current**

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

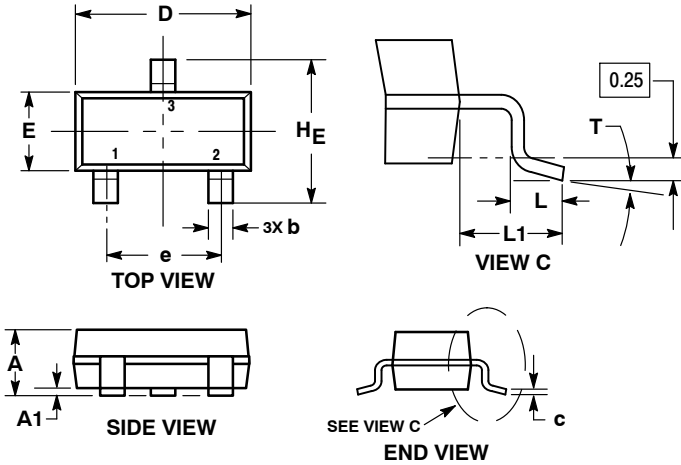
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**SOT-23 (TO-236)**  
**CASE 318-08**  
**ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1

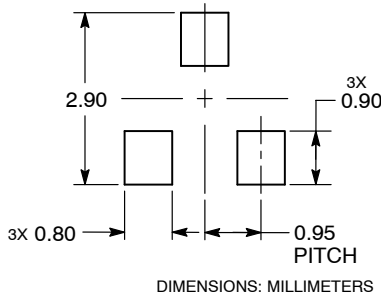


**NOTES:**

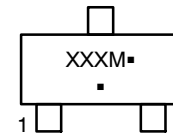
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS |      |      | INCHES |       |       |
|-----|-------------|------|------|--------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN    | NOM   | MAX   |
| A   | 0.89        | 1.00 | 1.11 | 0.035  | 0.039 | 0.044 |
| A1  | 0.01        | 0.06 | 0.10 | 0.000  | 0.002 | 0.004 |
| b   | 0.37        | 0.44 | 0.50 | 0.015  | 0.017 | 0.020 |
| c   | 0.08        | 0.14 | 0.20 | 0.003  | 0.006 | 0.008 |
| D   | 2.80        | 2.90 | 3.04 | 0.110  | 0.114 | 0.120 |
| E   | 1.20        | 1.30 | 1.40 | 0.047  | 0.051 | 0.055 |
| e   | 1.78        | 1.90 | 2.04 | 0.070  | 0.075 | 0.080 |
| L   | 0.30        | 0.43 | 0.55 | 0.012  | 0.017 | 0.022 |
| L1  | 0.35        | 0.54 | 0.69 | 0.014  | 0.021 | 0.027 |
| HE  | 2.10        | 2.40 | 2.64 | 0.083  | 0.094 | 0.104 |
| T   | 0°          | ---  | 10°  | 0°     | ---   | 10°   |

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- |   |   |   |  |
|---|---|---|--|
| STYLE 1 THRU 5:<br>CANCELLED                                | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR       | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE |
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE           | STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 12:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE      |
| STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE           | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          | STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE          | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE      |
| STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE         |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN           | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT         | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE          |
| STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE          | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION | STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE     | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE          |

|                         |                        |  |
|-------------------------|------------------------|--|
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| <b>DESCRIPTION:</b>     | <b>SOT-23 (TO-236)</b> | <b>PAGE 1 OF 1</b>   |

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